



BSS84WQ

P-Channel Enhancement Mode Field Effect Transistor

Product Summary

- V_{DS}
- I_D
- $R_{DS(ON)}$ (at $V_{GS}=-10V$)
- $R_{DS(ON)}$ (at $V_{GS}=-4.5V$)

-60 V

-0.19A

3.6 ohm

4.5 ohm

$T_A=100$

General Description

- Trench Power LV MOSFET technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free
- Part no. with suffix "Q" means

Ordering Information

PREFERRED P/N	PACKING CODE	
BSS84WQ	F2	

Applications

- $N = 1$ 3 Pin TO-18

	I_{DS}	-60	V
Gate-source Voltage	V_{GS}	± 20	V

$T_A=25$ @ Steady State

-0.19

Drain Current

I_D

A



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■ Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-60V, V_{GS}=0V$ Stati=				

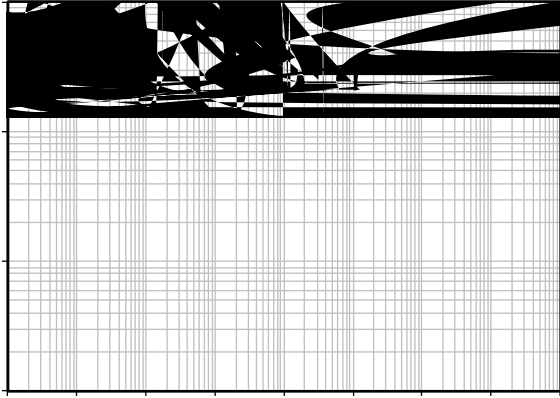


Figure 13. Maximum Transient Thermal Impedance

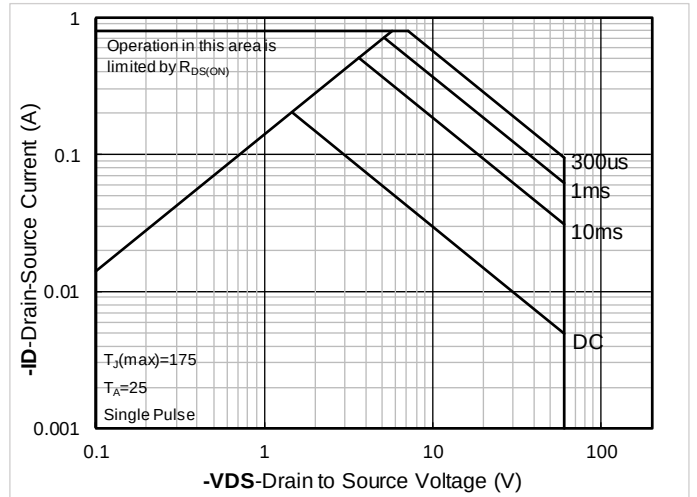


Figure 14. Safe Operation Area

v

'LVFODLPHU

7KH LQIRUPDWLRQ SURGXFWLRQ LQ IRWLVKHQJHQRK<RQJMLH (OHFWURQLF 7HHKQRO
ULJKW WR PDNH FKDLQHVRZLWKRXWSKRLSURGXFWV FGLWSOD\HG KHUHLQ WURGLPSURY
RU RWKHUZZLVH

7KH SURGXFW OLVWJQHGHWRILEQLXWBGHZLWKFBXDRQQRWLYGHVLJQHG IRU XVH LQ PHG
VDYLQJ OLIHVXVWDLQDQJMRH RUODQDQHDROXIPMV EIRKUHVSRQOLELQIEW\BQWGGPDUH
P VXFK LPSURSHU XVH RI VDOH

7KLV SXEOLFDWLRQ SXVSHUW DGDLQURUPDWSRQLSGHYRURXDGIRQLFQDODVQWRUPLW RX
KWVZZ \DQJMLHRRRPRQVXOW \RXHUHQVDOHWWRDLQJMLRWDQBWKHU D